

Lead (Pb) Free Product – RoHS Compliant

L470-30M32

 stem type LED with ball lens

L470-30M32 is an InGaN LED mounted on TO-18 stem with ball glass lens, being designed for sensing devices.

On forward bias it emits a spectral band of radiation, which peaks at 465nm.

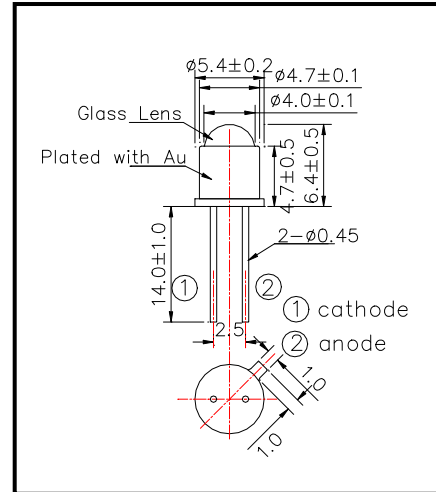
◆ Outer dimension (Unit:mm)

◆ Features

- 1) High Power
- 2) High Reliability

◆ Specifications

- 1) Product Name LED Lamp
- 2) Type No. L470-30M32
- 3) Chip Spec.
- (1) Material InGaN
- (2) Peak Wavelength 465nm
- 4) Package
- (1) Type TO-18 stem
- (2) Lens Ball Glass Lens



◆ Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature
Power Dissipation	P _D	200	mW	T _a =25°C
Forward Current	I _F	50	mA	T _a =25°C
Pulse Forward Current	I _{FP}	100	mA	T _a =25°C
Reverse Voltage	V _R	5	V	T _a =25°C
Operating Temperature	T _{OPR}	-30 ~ +85	°C	
Storage Temperature	T _{STG}	-30 ~ +100	°C	
Soldering Temperature	T _{SOL}	265	°C	

‡Pulse Forward Current condition: Duty=1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	V _F	I _F =20mA		3.2	4.0	V
Reverse Current	I _R	V _R =5V			10	uA
Total Radiated Power	P _O	I _F =20mA	3.5	5.5		mW
Brightness	I _V	I _F =20mA		4		cd
Radiant Intensity	I _E	I _F =20mA		30		mW/sr
Peak Wavelength	λ _P	I _F =20mA	455	465	475	nm
Half Width	Δλ	I _F =20mA		25		nm
Viewing Half Angle	θ _{1/2}	I _F =20mA		±10		deg.

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.